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a conductive layer substantially covering the surface;
a plurality of conductors on the surface defined by a plurality of grooves comprising ablated portions of the conductive layer, the conductors comprising portions of the conductive layer electrically isolated by the grooves and separated by remaining portions of the conductive layer having edges defined by the grooves; and
at least one semiconductor die on the substrate in electrical communication with the conductors.

30. (five times amended) A semiconductor component comprising:

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a substrate having a surface;
a conductive layer comprising a metal foil attached to and substantially covering the surface;
a plurality of conductors on the surface defined by a plurality of grooves comprising ablated portions of the metal foil, each conductor comprising a portion of the metal foil electrically isolated by at least one pair of grooves and separated from an adjacent conductor by a remaining portion of the metal foil; and
a semiconductor die flip chip mounted or wire bonded to the substrate in electrical communication with the conductors.

35. (five times amended) A semiconductor component comprising:

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a substrate having a surface;
a conductive layer substantially covering the surface;
a plurality of conductors on the surface comprising portions of the conductive layer separated by remaining portions of the conductive layer, the conductors defined and electrically isolated by a plurality of grooves comprising ablated portions of the conductive layer, each conductor and each remaining portion defined by at least one pair of grooves;

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a semiconductor die on the substrate in electrical communication with the conductors.

47. (five times amended) A semiconductor component comprising:

a substrate having a surface;

a conductive layer substantially covering the surface;

and

a plurality of conductors on the surface defined by a plurality of grooves comprising ablated portions of the conductive layer, the conductors comprising portions of the conductive layer which are electrically isolated from one another by the grooves and separated by remaining portions of the substrate having edges defined by the grooves, the conductors comprising first contacts on first ends thereof and second contacts on second ends thereof; and

a semiconductor die on the substrate bonded to the first contacts.

52. (four times amended) A semiconductor component comprising:

a substrate having a surface;

a conductive layer substantially covering the surface;

a plurality of conductors on the surface defined by a plurality of grooves comprising ablated portions of the conductive layer, the conductors comprising portions of the conductive layer electrically isolated by the grooves and separated by remaining portions of the conductive layer having edges defined by the grooves;

a plurality of conductive vias through the substrate in electrical communication with the conductors; and

a semiconductor die on the substrate in electrical communication with the conductors.

Clean Version Of All Pending Claims

25. (five times amended) A semiconductor component comprising:

a substrate having a surface;

a conductive layer substantially covering the surface;

a plurality of conductors on the surface defined by a plurality of grooves comprising ablated portions of the conductive layer, the conductors comprising portions of the conductive layer electrically isolated by the grooves and separated by remaining portions of the conductive layer having edges defined by the grooves; and

at least one semiconductor die on the substrate in electrical communication with the conductors.

26. (thrice amended) The semiconductor component of claim 25 wherein the conductors comprise a plurality of pads and the semiconductor die is wire bonded to the pads.

27. (thrice amended) The semiconductor component of claim 25 wherein the semiconductor die is flip chip mounted to the conductors.

28. (twice amended) The semiconductor component of claim 25 wherein the substrate comprises a material selected from the group consisting of plastic, glass filled resin, silicon, ceramic, metal, germanium, and gallium arsenide.

29. (twice amended) The semiconductor component of claim 25 wherein the conductors comprise a plurality of contacts adapted for electrical connection to outside circuitry.

30. (five times amended) A semiconductor component comprising:

a substrate having a surface;

a conductive layer comprising a metal foil attached to and substantially covering the surface;

a plurality of conductors on the surface defined by a plurality of grooves comprising ablated portions of the metal foil, each conductor comprising a portion of the metal foil electrically isolated by at least one pair of grooves and separated from an adjacent conductor by a remaining portion of the metal foil; and

a semiconductor die flip chip mounted or wire bonded to the substrate in electrical communication with the conductors.

31. (twice amended) The semiconductor component of claim 30 further comprising a plurality of contacts on the conductors adapted for electrical connection to outside circuitry.

32. (twice amended) The semiconductor component of claim 30 further comprising a plurality of conductive vias in the substrate in electrical communication with the conductors and with a plurality of contact balls on a second surface of the substrate.

33. (twice amended) The semiconductor component of claim 30 wherein the component comprises a chip module, a multi chip module or a package.

34. (twice amended) The semiconductor component of claim 30 further comprising an encapsulant at least partially covering the semiconductor die and at least a portion of the surface.

35. (five times amended) A semiconductor component comprising:

a substrate having a surface;

a conductive layer substantially covering the surface;

a plurality of conductors on the surface comprising portions of the conductive layer separated by remaining portions of the conductive layer, the conductors defined and electrically isolated by a plurality of grooves comprising ablated portions of the conductive layer, each conductor and each remaining portion defined by at least one pair of grooves;

a semiconductor die on the substrate in electrical communication with the conductors.

36. (thrice amended) The semiconductor component of claim 35 wherein the die is flip chip mounted or wire bonded to the conductors.

37. (twice amended) The semiconductor component of claim 35 wherein the conductors comprise pads bonded to the die and contacts adapted for electrical connection to outside circuitry.

38. (twice amended) The semiconductor component of claim 35 wherein the substrate comprises a semiconductor material and an electrically insulating layer on the surface.

39. (twice amended) The semiconductor component of claim 35 wherein the substrate comprises a material selected from the group consisting of plastic, glass filled resin, ceramic, silicon, metal, germanium, and gallium arsenide.

47. (five times amended) A semiconductor component comprising:

a substrate having a surface;

a conductive layer substantially covering the surface;

and

a plurality of conductors on the surface defined by a plurality of grooves comprising ablated portions of the conductive layer, the conductors comprising portions of the conductive layer which are electrically isolated from one another by the grooves and separated by remaining portions of the substrate having edges defined by the grooves, the conductors comprising first contacts on first ends thereof and second contacts on second ends thereof; and

a semiconductor die on the substrate bonded to the first contacts.

48. (amended) The semiconductor component of claim 47 wherein the semiconductor die is flip chip mounted or wire bonded to the first contacts.

49. (amended) The semiconductor component of claim 47 wherein each conductor has a first width of about 5 μm .

50. (amended) The semiconductor component of claim 47 wherein each groove has a second width of about 5 μm .

51. (amended) The semiconductor component of claim 47 wherein the conductive layer includes an opening for attaching the die to the substrate.

52. (four times amended) A semiconductor component comprising:

a substrate having a surface;

a conductive layer substantially covering the surface;

a plurality of conductors on the surface defined by a plurality of grooves comprising ablated portions of the conductive layer, the conductors comprising portions of the conductive layer electrically isolated by the grooves and separated by remaining portions of the conductive layer having edges defined by the grooves;

a plurality of conductive vias through the substrate in electrical communication with the conductors; and
a semiconductor die on the substrate in electrical communication with the conductors.

53. (amended) The semiconductor component of claim 52 further comprising a plurality of contact balls on the substrate in electrical communication with the conductive vias and arranged in a ball grid array.